TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

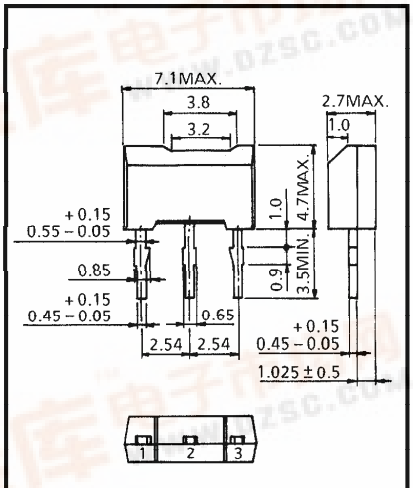
2SA1926

POWER AMPLIFIER APPLICATIONS.

POWER SWITCHING APPLICATIONS.

- Low Collector Saturation Voltage
  : $V_{CE\ (sat)} = -0.17V$ (Max.) ($I_C = -1A$)

Unit in mm



1. BASE
2. COLLECTOR
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-7D101A

Weight : 0.2g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−80	V
Collector-Emitter Voltage	V_{CEO}	−80	V
Emitter-Base Voltage	V_{EBO}	−8	V
Collector Current	I_C	−3	A
Base Current	I_B	−1	A
Collector Power Dissipation	P_C	1000	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -80V$, $I_E = 0$	—	—	−1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -8V$, $I_C = 0$	—	—	−1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)\ CEO}$	$I_C = -10mA$, $I_B = 0$	−80	—	—	V
DC Current Gain	$h_{FE\ (1)}$	$V_{CE} = -2V$, $I_C = -0.5A$	150	—	400	
	$h_{FE\ (2)}$	$V_{CE} = -2V$, $I_C = -1.5A$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	$I_C = -1A$, $I_B = -0.05A$	—	—	−0.17	V
Base-Emitter Saturation Voltage	$V_{BE\ (sat)}$	$I_C = -1A$, $I_B = -0.05A$	—	—	−1.2	V
Transition Frequency	f_T	$V_{CE} = -2V$, $I_C = -0.5A$	—	80	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V$, $I_E = 0$, f = 1MHz	—	45	—	pF

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